

# IS61WV20488ALL IS61/64WV20488BLL



## 2M x 8 HIGH-SPEED CMOS STATIC RAM

AUGUST 2010

### FEATURES

- High-speed access times:  
8, 10, 20 ns
- High-performance, low-power CMOS process
- Multiple center power and ground pins for greater noise immunity
- Easy memory expansion with  $\overline{CE}$  and  $\overline{OE}$  options
- $\overline{CE}$  power-down
- Fully static operation: no clock or refresh required
- TTL compatible inputs and outputs
- Single power supply
  - V<sub>DD</sub> 1.65V to 2.2V (IS61WV20488ALL)  
speed = 20ns for V<sub>cc</sub> = 1.65V to 2.2V
  - V<sub>DD</sub> 2.4V to 3.6V (IS61/64WV20488BLL)  
speed = 10ns for V<sub>cc</sub> = 2.4V to 3.6V  
speed = 8ns for V<sub>cc</sub> = 3.3V ± 5%
- Packages available:
  - 48-ball miniBGA (9mm x 11mm)
  - 44-pin TSOP (Type II)
- Industrial and Automotive Temperature Support
- Lead-free available

### DESCRIPTION

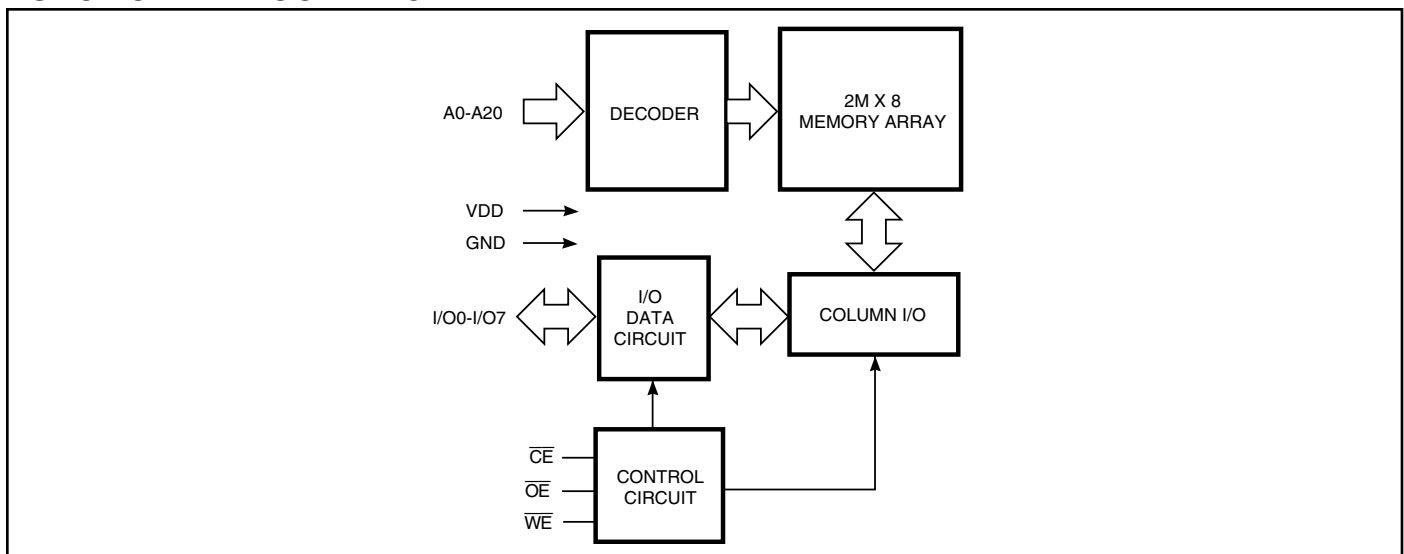
The *ISSI* IS61WV20488ALL/BLL and IS64WV20488BLL are very high-speed, low power, 2M-word by 8-bit CMOS static RAM. The IS61WV20488ALL/BLL and IS64WV20488BLL are fabricated using *ISSI*'s high-performance CMOS technology. This highly reliable process coupled with innovative circuit design techniques, yields higher performance and low power consumption devices.

When  $\overline{CE}$  is HIGH (deselected), the device assumes a standby mode at which the power dissipation can be reduced down with CMOS input levels.

The IS61WV20488ALL/BLL and IS64WV20488BLL operate from a single power supply and all inputs are TTL-compatible.

The IS61WV20488ALL/BLL and IS64WV20488BLL are available in 48 ball mini BGA and 44-pin TSOP (Type II) packages.

### FUNCTIONAL BLOCK DIAGRAM



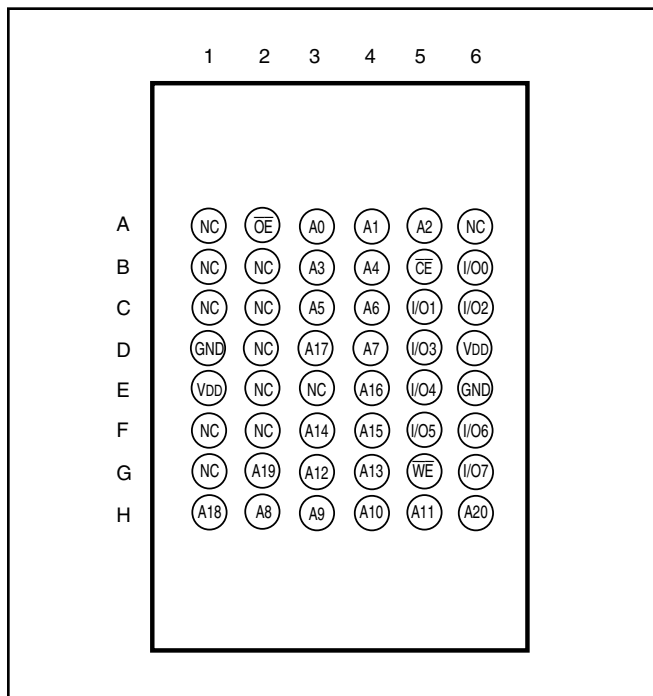
Copyright © 2010 Integrated Silicon Solution, Inc. All rights reserved. ISSI reserves the right to make changes to this specification and its products at any time without notice. ISSI assumes no liability arising out of the application or use of any information, products or services described herein. Customers are advised to obtain the latest version of this device specification before relying on any published information and before placing orders for products.

Integrated Silicon Solution, Inc. does not recommend the use of any of its products in life support applications where the failure or malfunction of the product can reasonably be expected to cause failure of the life support system or to significantly affect its safety or effectiveness. Products are not authorized for use in such applications unless Integrated Silicon Solution, Inc. receives written assurance to its satisfaction, that:

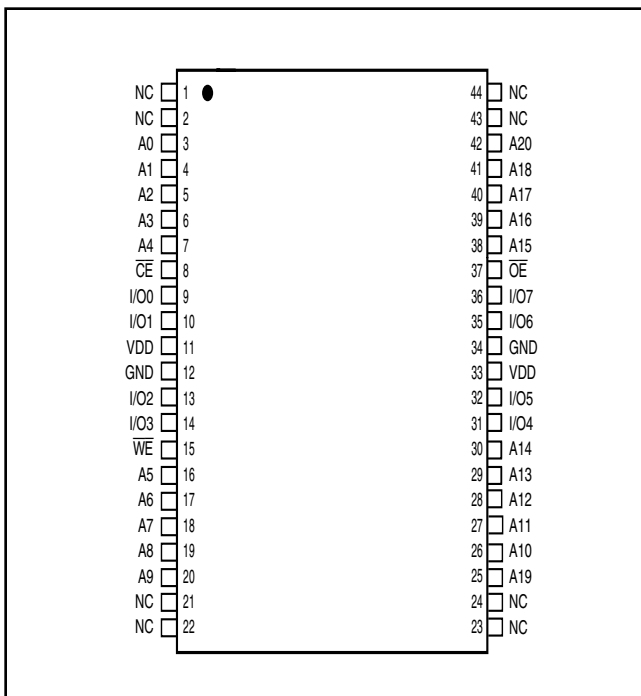
- a.) the risk of injury or damage has been minimized;
- b.) the user assume all such risks; and
- c.) potential liability of Integrated Silicon Solution, Inc is adequately protected under the circumstances

**PIN CONFIGURATION**

**48-pin Mini BGA (M ) (9mm x 11mm)**



**44-pin TSOP (Type II )**



**PIN DESCRIPTIONS**

A0-A20	Address Inputs
$\overline{CE}$	Chip Enable Input
$\overline{OE}$	Output Enable Input
$\overline{WE}$	Write Enable Input
I/O0-I/O7	Data Input / Output
VDD	Power
GND	Ground
NC	No Connection

**TRUTH TABLE**

Mode	$\overline{WE}$	$\overline{CE}$	$\overline{OE}$	I/O Operation	V <sub>DD</sub> Current
Not Selected (Power-down)	X	H	X	High-Z	I <sub>SB1</sub> , I <sub>SB2</sub>
Output Disabled	H	L	H	High-Z	I <sub>CC</sub>
Read	H	L	L	D <sub>OUT</sub>	I <sub>CC</sub>
Write	L	L	X	D <sub>IN</sub>	I <sub>CC</sub>

**ABSOLUTE MAXIMUM RATINGS<sup>(1)</sup>**

Symbol	Parameter	Value	Unit
V <sub>TERM</sub>	Terminal Voltage with Respect to GND	-0.5 to V <sub>DD</sub> + 0.5	V
V <sub>DD</sub>	V <sub>DD</sub> Relates to GND	-0.3 to 4.0	V
T <sub>STG</sub>	Storage Temperature	-65 to +150	°C
P <sub>T</sub>	Power Dissipation	1.0	W

**Notes:**

1. Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

**CAPACITANCE<sup>(1,2)</sup>**

Symbol	Parameter	Conditions	Max.	Unit
C <sub>IN</sub>	Input Capacitance	V <sub>IN</sub> = 0V	6	pF
C <sub>I/O</sub>	Input/Output Capacitance	V <sub>OUT</sub> = 0V	8	pF

**Notes:**

1. Tested initially and after any design or process changes that may affect these parameters.
2. Test conditions: T<sub>A</sub> = 25°C, f = 1 MHz, V<sub>DD</sub> = 3.3V.

**OPERATING RANGE (V<sub>DD</sub>) (IS61WV20488ALL)**

Range	Ambient Temperature	V <sub>DD</sub> (20 ns)
Commercial	0°C to +70°C	1.65V-2.2V
Industrial	-40°C to +85°C	1.65V-2.2V
Automotive	-40°C to +125°C	1.65V-2.2V

**OPERATING RANGE (V<sub>DD</sub>) (IS61WV20488BLL)<sup>(1)</sup>**

Range	Ambient Temperature	V <sub>DD</sub> (8 ns)	V <sub>DD</sub> (10 ns)
Commercial	0°C to +70°C	3.3V ± 5%	2.4V-3.6V
Industrial	-40°C to +85°C	3.3V ± 5%	2.4V-3.6V

**Note:**

1. When operated in the range of 2.4V-3.6V, the device meets 10ns. When operated in the range of 3.3V ± 5%, the device meets 8ns.

**OPERATING RANGE (V<sub>DD</sub>) (IS64WV20488BLL)**

Range	Ambient Temperature	V <sub>DD</sub> (10 ns)
Automotive	-40°C to +125°C	2.4V-3.6V

**DC ELECTRICAL CHARACTERISTICS** (Over Operating Range)

 **$V_{DD} = 3.3V \pm 5\%$** 

Symbol	Parameter	Test Conditions	Min.	Max.	Unit
$V_{OH}$	Output HIGH Voltage	$V_{DD} = \text{Min.}, I_{OH} = -4.0 \text{ mA}$	2.4	—	V
$V_{OL}$	Output LOW Voltage	$V_{DD} = \text{Min.}, I_{OL} = 8.0 \text{ mA}$	—	0.4	V
$V_{IH}$	Input HIGH Voltage		2	$V_{DD} + 0.3$	V
$V_{IL}$	Input LOW Voltage <sup>(1)</sup>		-0.3	0.8	V
$I_{LI}$	Input Leakage	$GND \leq V_{IN} \leq V_{DD}$	-1	1	$\mu\text{A}$
$I_{LO}$	Output Leakage	$GND \leq V_{OUT} \leq V_{DD}$ , Outputs Disabled	-1	1	$\mu\text{A}$

**Note:**

- $V_{IL} (\text{min.}) = -0.3V \text{ DC}; V_{IL} (\text{min.}) = -2.0V \text{ AC}$  (pulse width 2.0 ns). Not 100% tested.  
 $V_{IH} (\text{max.}) = V_{DD} + 0.3V \text{ DC}; V_{IH} (\text{max.}) = V_{DD} + 2.0V \text{ AC}$  (pulse width 2.0 ns). Not 100% tested.

**DC ELECTRICAL CHARACTERISTICS** (Over Operating Range)

 **$V_{DD} = 2.4V-3.6V$** 

Symbol	Parameter	Test Conditions	Min.	Max.	Unit
$V_{OH}$	Output HIGH Voltage	$V_{DD} = \text{Min.}, I_{OH} = -1.0 \text{ mA}$	1.8	—	V
$V_{OL}$	Output LOW Voltage	$V_{DD} = \text{Min.}, I_{OL} = 1.0 \text{ mA}$	—	0.4	V
$V_{IH}$	Input HIGH Voltage		2.0	$V_{DD} + 0.3$	V
$V_{IL}$	Input LOW Voltage <sup>(1)</sup>		-0.3	0.8	V
$I_{LI}$	Input Leakage	$GND \leq V_{IN} \leq V_{DD}$	-1	1	$\mu\text{A}$
$I_{LO}$	Output Leakage	$GND \leq V_{OUT} \leq V_{DD}$ , Outputs Disabled	-1	1	$\mu\text{A}$

**Note:**

- $V_{IL} (\text{min.}) = -0.3V \text{ DC}; V_{IL} (\text{min.}) = -2.0V \text{ AC}$  (pulse width 2.0 ns). Not 100% tested.  
 $V_{IH} (\text{max.}) = V_{DD} + 0.3V \text{ DC}; V_{IH} (\text{max.}) = V_{DD} + 2.0V \text{ AC}$  (pulse width 2.0 ns). Not 100% tested.

**DC ELECTRICAL CHARACTERISTICS** (Over Operating Range)

 **$V_{DD} = 1.65V-2.2V$** 

Symbol	Parameter	Test Conditions	$V_{DD}$	Min.	Max.	Unit
$V_{OH}$	Output HIGH Voltage	$I_{OH} = -0.1 \text{ mA}$	1.65-2.2V	1.4	—	V
$V_{OL}$	Output LOW Voltage	$I_{OL} = 0.1 \text{ mA}$	1.65-2.2V	—	0.2	V
$V_{IH}$	Input HIGH Voltage		1.65-2.2V	1.4	$V_{DD} + 0.2$	V
$V_{IL}^{(1)}$	Input LOW Voltage		1.65-2.2V	-0.2	0.4	V
$I_{LI}$	Input Leakage	$GND \leq V_{IN} \leq V_{DD}$		-1	1	$\mu\text{A}$
$I_{LO}$	Output Leakage	$GND \leq V_{OUT} \leq V_{DD}$ , Outputs Disabled		-1	1	$\mu\text{A}$

**Note:**

- $V_{IL} (\text{min.}) = -0.3V \text{ DC}; V_{IL} (\text{min.}) = -2.0V \text{ AC}$  (pulse width 2.0 ns). Not 100% tested.  
 $V_{IH} (\text{max.}) = V_{DD} + 0.3V \text{ DC}; V_{IH} (\text{max.}) = V_{DD} + 2.0V \text{ AC}$  (pulse width 2.0 ns). Not 100% tested.

**AC TEST CONDITIONS (HIGH SPEED)**

Parameter	Unit (2.4V-3.6V)	Unit (3.3V ± 5%)	Unit (1.65V-2.2V)
Input Pulse Level	0.4V to $V_{DD}-0.3V$	0.4V to $V_{DD}-0.3V$	0.4V to $V_{DD}-0.2V$
Input Rise and Fall Times	1.5ns	1.5ns	1.5ns
Input and Output Timing and Reference Level ( $V_{Ref}$ )	$V_{DD}/2$	$V_{DD}/2 + 0.05$	$V_{DD}/2$
Output Load	See Figures 1 and 2	See Figures 1 and 2	See Figures 1 and 2

**AC TEST LOADS**

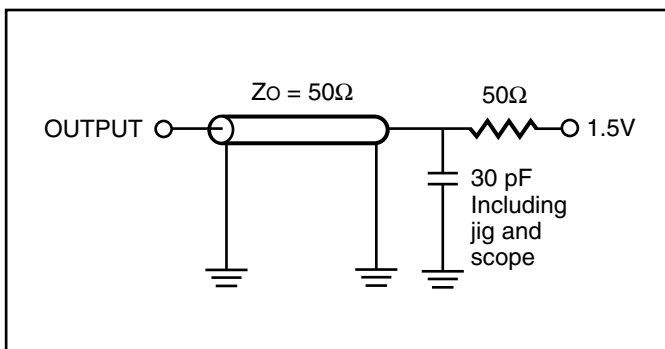


Figure 1.

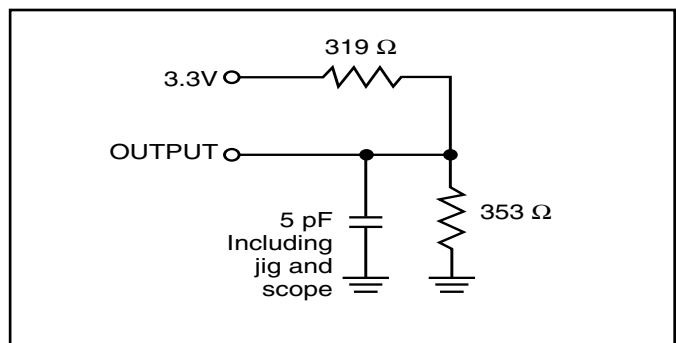


Figure 2.

**POWER SUPPLY CHARACTERISTICS<sup>(1)</sup>** (Over Operating Range)

Symbol	Parameter	Test Conditions		-8		-10		-20		Unit
				Min.	Max.	Min.	Max.	Min.	Max.	
I <sub>CC</sub>	V <sub>DD</sub> Dynamic Operating Supply Current	V <sub>DD</sub> = Max., I <sub>OUT</sub> = 0 mA, f = f <sub>MAX</sub>	Com.	—	120	—	95	—	90	mA
			Ind.	—	125	—	100	—	100	
			Auto.	—	—	—	140	—	140	
			typ. <sup>(2)</sup>			60				
I <sub>CC1</sub>	Operating Supply Current	V <sub>DD</sub> = Max., I <sub>OUT</sub> = 0 mA, f = 0	Com.	—	35	—	30	—	30	mA
			Ind.	—	35	—	40	—	40	
			Auto.	—	—	—	60	—	70	
I <sub>SB1</sub>	TTL Standby Current (TTL Inputs)	V <sub>DD</sub> = Max., V <sub>IN</sub> = V <sub>IH</sub> or V <sub>IL</sub> CE ≥ V <sub>IH</sub> , f = 0	Com.	—	30	—	30	—	30	mA
			Ind.	—	35	—	35	—	35	
			Auto.	—	—	—	70	—	70	
I <sub>SB2</sub>	CMOS Standby Current (CMOS Inputs)	V <sub>DD</sub> = Max., CE ≥ V <sub>DD</sub> - 0.2V, V <sub>IN</sub> ≥ V <sub>DD</sub> - 0.2V, or V <sub>IN</sub> ≤ 0.2V, f = 0	Com.	—	20	—	20	—	15	mA
			Ind.	—	25	—	25	—	20	
			Auto.	—	—	—	70	—	70	
			typ. <sup>(2)</sup>			4				

**Note:**

- At f = f<sub>MAX</sub>, address and data inputs are cycling at the maximum frequency, f = 0 means no input lines change.
- Typical values are measured at V<sub>DD</sub> = 3.0V, T<sub>A</sub> = 25°C and not 100% tested.

**READ CYCLE SWITCHING CHARACTERISTICS<sup>(1)</sup> (Over Operating Range)**

Symbol	Parameter	-8		-10		Unit
		Min.	Max.	Min.	Max.	
t <sub>RC</sub>	Read Cycle Time	8	—	10	—	ns
t <sub>AA</sub>	Address Access Time	—	8	—	10	ns
t <sub>OHA</sub>	Output Hold Time	2	—	2	—	ns
t <sub>ACE</sub>	$\overline{\text{CE}}$ Access Time	—	8	—	10	ns
t <sub>DOE</sub>	$\overline{\text{OE}}$ Access Time	—	5.5	—	6.5	ns
t <sub>HZOE<sup>(2)</sup></sub>	$\overline{\text{OE}}$ to High-Z Output	—	3	—	4	ns
t <sub>LZOE<sup>(2)</sup></sub>	$\overline{\text{OE}}$ to Low-Z Output	0	—	0	—	ns
t <sub>HZCE<sup>(2)</sup></sub>	$\overline{\text{CE}}$ to High-Z Output	0	3	0	4	ns
t <sub>LZCE<sup>(2)</sup></sub>	$\overline{\text{CE}}$ to Low-Z Output	3	—	3	—	ns
t <sub>PU</sub>	Power Up Time	0	—	0	—	ns
t <sub>PD</sub>	Power Down Time	—	8	—	10	ns

**Notes:**

1. Test conditions assume signal transition times of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0V to 3.0V and output loading specified in Figure 1.
2. Tested with the load in Figure 2. Transition is measured  $\pm 500$  mV from steady-state voltage.



**READ CYCLE SWITCHING CHARACTERISTICS<sup>(1)</sup>** (Over Operating Range)

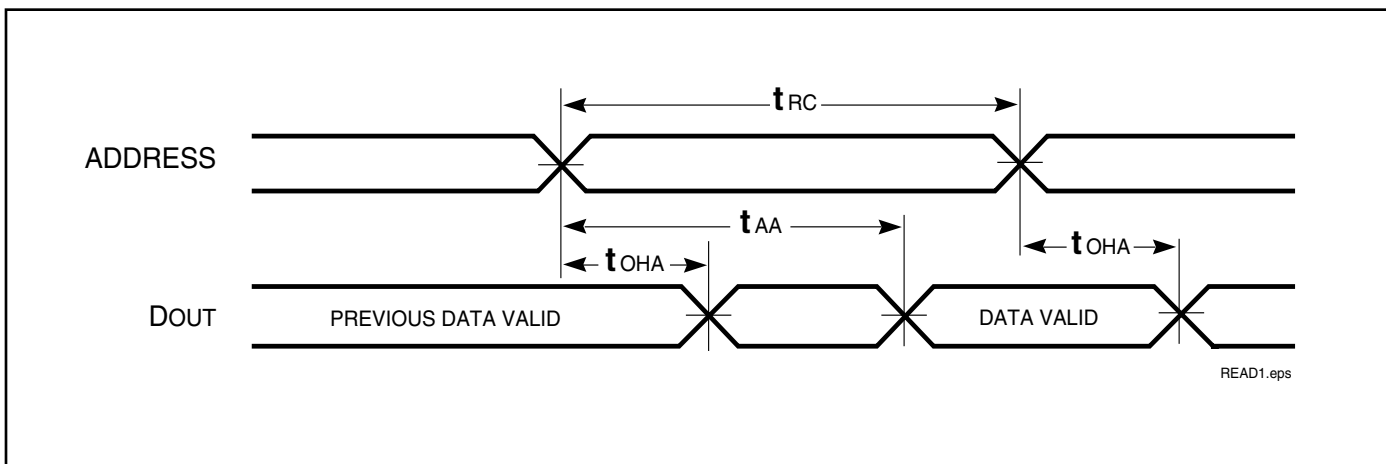
Symbol	Parameter	-20 ns		Unit
		Min.	Max.	
t <sub>RC</sub>	Read Cycle Time	20	—	ns
t <sub>AA</sub>	Address Access Time	—	20	ns
t <sub>OHA</sub>	Output Hold Time	2.5	—	ns
t <sub>ACE</sub>	$\overline{CE}$ Access Time	—	20	ns
t <sub>DOE</sub>	$\overline{OE}$ Access Time	—	8	ns
t <sub>HZOE<sup>(2)</sup></sub>	$\overline{OE}$ to High-Z Output	0	8	ns
t <sub>LZOE<sup>(2)</sup></sub>	$\overline{OE}$ to Low-Z Output	0	—	ns
t <sub>HZCE<sup>(2)</sup></sub>	$\overline{CE}$ to High-Z Output	0	8	ns
t <sub>LZCE<sup>(2)</sup></sub>	$\overline{CE}$ to Low-Z Output	3	—	ns
t <sub>PU</sub>	Power Up Time	0	—	ns
t <sub>PD</sub>	Power Down Time	—	20	ns

**Notes:**

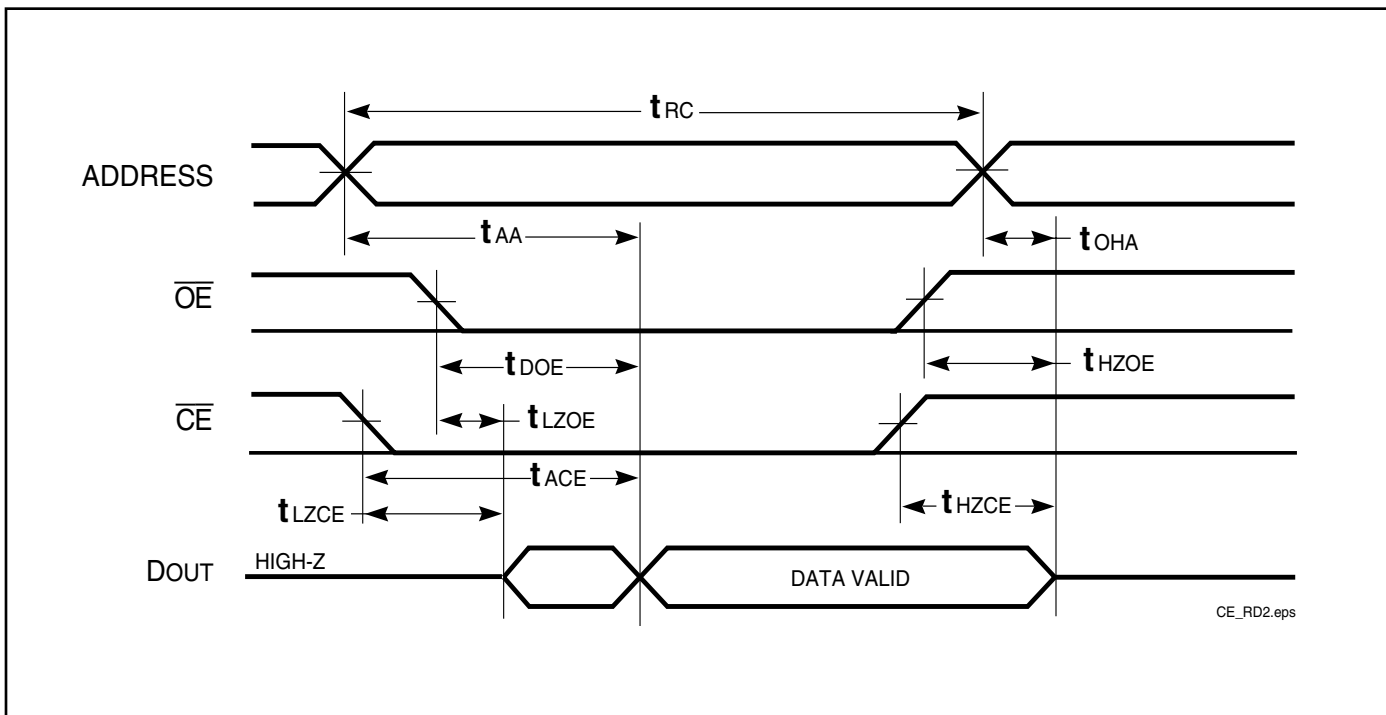
1. Test conditions assume signal transition times of 1.5 ns or less, timing reference levels of 1.25V, input pulse levels of 0.4V to V<sub>DD</sub>-0.3V and output loading specified in Figure 1.
2. Tested with the load in Figure 2. Transition is measured ±500 mV from steady-state voltage. Not 100% tested.
3. Not 100% tested.

**AC WAVEFORMS**

**READ CYCLE NO. 1<sup>(1,2)</sup>** (Address Controlled) ( $\overline{CE} = \overline{OE} = V_{IL}$ )



**READ CYCLE NO. 2<sup>(1,3)</sup>** ( $\overline{CE}$  and  $\overline{OE}$  Controlled)



**Notes:**

1.  $\overline{WE}$  is HIGH for a Read Cycle.
2. The device is continuously selected.  $\overline{OE}$ ,  $\overline{CE} = V_{IL}$ .
3. Address is valid prior to or coincident with  $\overline{CE}$  LOW transitions.

**WRITE CYCLE SWITCHING CHARACTERISTICS<sup>(1,3)</sup> (Over Operating Range)**

Symbol	Parameter	-8		-10		Unit
		Min.	Max.	Min.	Max.	
t <sub>WC</sub>	Write Cycle Time	8	—	10	—	ns
t <sub>SCE</sub>	$\overline{CE}$ to Write End	6.5	—	8	—	ns
t <sub>AW</sub>	Address Setup Time to Write End	6.5	—	8	—	ns
t <sub>HA</sub>	Address Hold from Write End	0	—	0	—	ns
t <sub>SA</sub>	Address Setup Time	0	—	0	—	ns
t <sub>PWE1</sub>	$\overline{WE}$ Pulse Width ( $\overline{OE}$ = HIGH)	6.5	—	8	—	ns
t <sub>PWE2</sub>	$\overline{WE}$ Pulse Width ( $\overline{OE}$ = LOW)	8.0	—	10	—	ns
t <sub>SD</sub>	Data Setup to Write End	5	—	6	—	ns
t <sub>HD</sub>	Data Hold from Write End	0	—	0	—	ns
t <sub>HZWE<sup>(2)</sup></sub>	$\overline{WE}$ LOW to High-Z Output	—	3.5	—	5	ns
t <sub>LZWE<sup>(2)</sup></sub>	$\overline{WE}$ HIGH to Low-Z Output	2	—	2	—	ns

**Notes:**

1. Test conditions assume signal transition times of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0V to 3.0V and output loading specified in Figure 1.
2. Tested with the load in Figure 2. Transition is measured  $\pm 500$  mV from steady-state voltage. Not 100% tested.
3. The internal write time is defined by the overlap of  $\overline{CE}$  LOW and  $\overline{WE}$  LOW. All signals must be in valid states to initiate a Write, but any one can go inactive to terminate the Write. The Data Input Setup and Hold timing are referenced to the rising or falling edge of the signal that terminates the write. Shaded area product in development

**WRITE CYCLE SWITCHING CHARACTERISTICS<sup>(1,2)</sup>** (Over Operating Range)

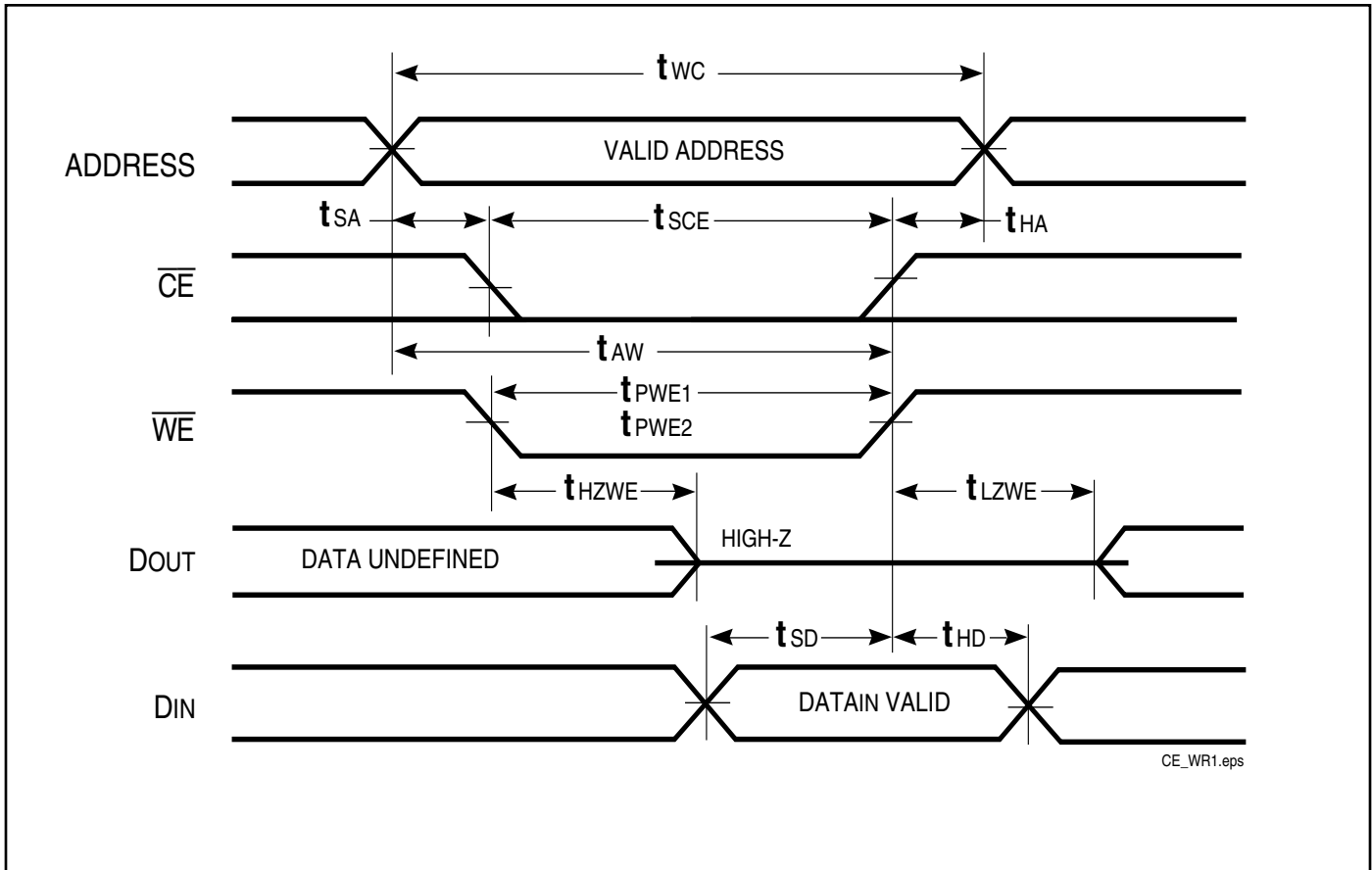
Symbol	Parameter	-20 ns		Unit
		Min.	Max.	
t <sub>WC</sub>	Write Cycle Time	20	—	ns
t <sub>SCE</sub>	$\overline{CE}$ to Write End	12	—	ns
t <sub>AW</sub>	Address Setup Time to Write End	12	—	ns
t <sub>HA</sub>	Address Hold from Write End	0	—	ns
t <sub>SA</sub>	Address Setup Time	0	—	ns
t <sub>PWE1</sub>	$\overline{WE}$ Pulse Width ( $\overline{OE}$ = HIGH)	12	—	ns
t <sub>PWE2</sub>	$\overline{WE}$ Pulse Width ( $\overline{OE}$ = LOW)	17	—	ns
t <sub>SD</sub>	Data Setup to Write End	9	—	ns
t <sub>HD</sub>	Data Hold from Write End	0	—	ns
t <sub>HZWE</sub> <sup>(3)</sup>	$\overline{WE}$ LOW to High-Z Output	—	9	ns
t <sub>LZWE</sub> <sup>(3)</sup>	$\overline{WE}$ HIGH to Low-Z Output	3	—	ns

**Notes:**

1. Test conditions assume signal transition times of 1.5ns or less, timing reference levels of 1.25V, input pulse levels of 0.4V to V<sub>DD</sub>-0.3V and output loading specified in Figure 1.
2. Tested with the load in Figure 2. Transition is measured  $\pm 500$  mV from steady-state voltage. Not 100% tested.
3. The internal write time is defined by the overlap of  $\overline{CE}$  LOW and  $\overline{WE}$  LOW. All signals must be in valid states to initiate a Write, but any one can go inactive to terminate the Write. The Data Input Setup and Hold timing are referenced to the rising or falling edge of the signal that terminates the write.

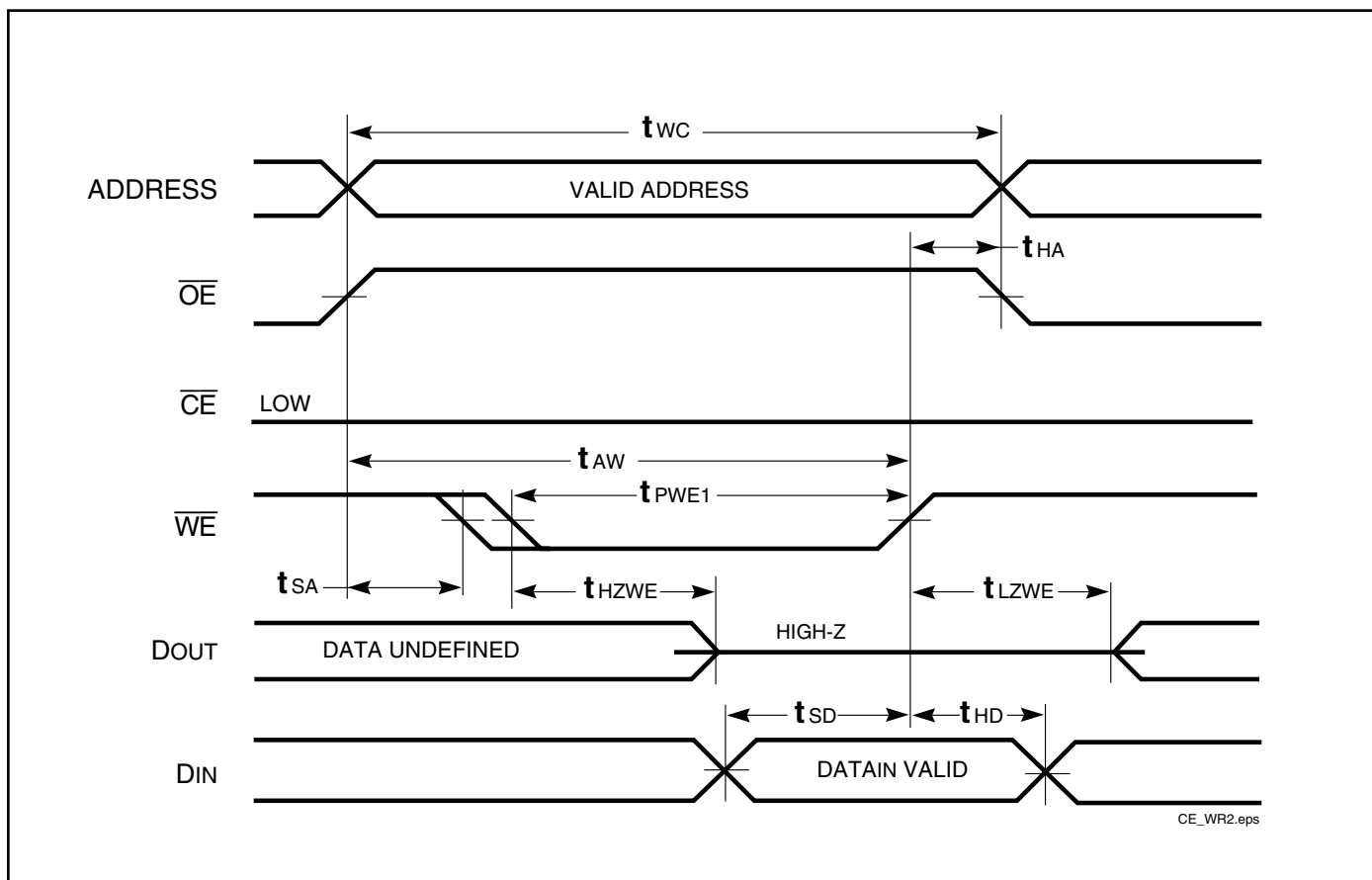
**AC WAVEFORMS**

**WRITE CYCLE NO. 1**<sup>(1,2)</sup> ( $\overline{CE}$  Controlled,  $\overline{OE}$  = HIGH or LOW)



**AC WAVEFORMS**

**WRITE CYCLE NO. 2<sup>(1,2)</sup>** ( $\overline{WE}$  Controlled:  $\overline{OE}$  is HIGH During Write Cycle)



**Notes:**

1. The internal write time is defined by the overlap of  $\overline{CE}$  LOW and  $\overline{WE}$  LOW. All signals must be in valid states to initiate a Write, but any one can go inactive to terminate the Write. The Data Input Setup and Hold timing are referenced to the rising or falling edge of the signal that terminates the Write.
2. I/O will assume the High-Z state if  $\overline{OE} > V_{IH}$ .

**AC WAVEFORMS**

**WRITE CYCLE NO. 3** ( $\overline{WE}$  Controlled:  $\overline{OE}$  is LOW During Write Cycle)



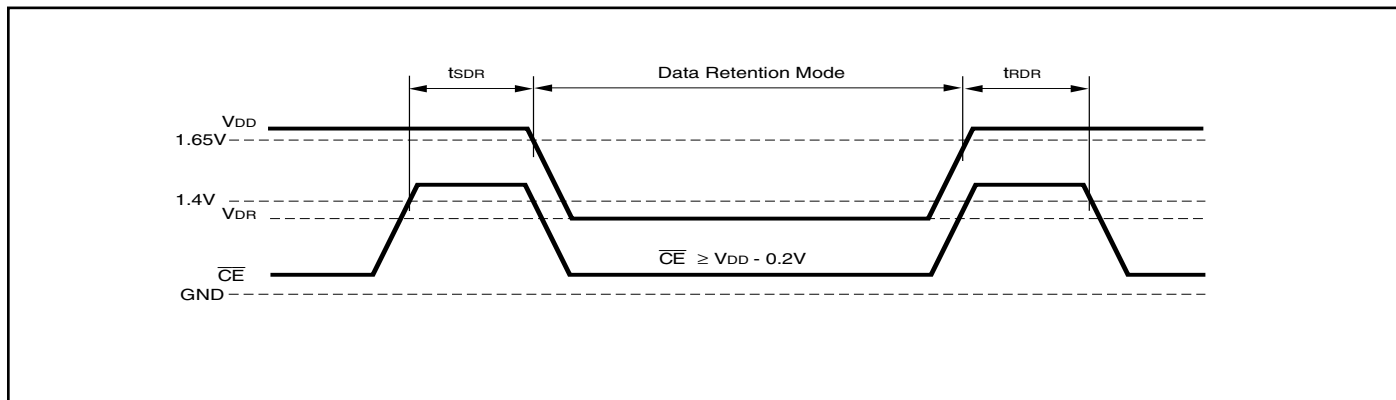
**DATA RETENTION SWITCHING CHARACTERISTICS**

Symbol	Parameter	Test Condition	Min.	Max.	Unit
V <sub>DR</sub>	V <sub>DD</sub> for Data Retention	See Data Retention Waveform	1.2	3.6	V
I <sub>DR</sub>	Data Retention Current	V <sub>DD</sub> = 1.2V, $\overline{CE} \geq V_{DD} - 0.2V$	Ind. Auto. typ. <sup>(1)</sup>	25 60 3	mA
t <sub>SDR</sub>	Data Retention Setup Time	See Data Retention Waveform	0	—	ns
t <sub>RDR</sub>	Recovery Time	See Data Retention Waveform	t <sub>RC</sub>	—	ns

**Note:**

1. Typical values are measured at V<sub>DD</sub> = 3.0V, T<sub>A</sub> = 25°C and not 100% tested.

**DATA RETENTION WAVEFORM ( $\overline{CE}$  Controlled)**





**ORDERING INFORMATION**
**Industrial Range: -40°C to +85°C**
**Voltage Range: 2.4V to 3.6V**

Speed (ns)	Order Part No.	Package
10 (8 <sup>1</sup> )	IS61WV20488BLL-10MI	48 mini BGA (9mm x 11mm)
	IS61WV20488BLL-10MLI	48 mini BGA (9mm x 11mm), Lead-free
	IS61WV20488BLL-10TI	TSOP (Type II)
	IS61WV20488BLL-10TLI	TSOP (Type II), Lead-free

**Note:**

 1. Speed = 8ns for  $V_{DD} = 3.3V \pm 5\%$ . Speed = 10ns for  $V_{DD} = 2.4V$  to  $3.3V$ .

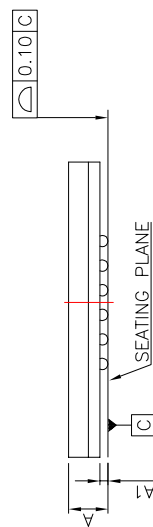
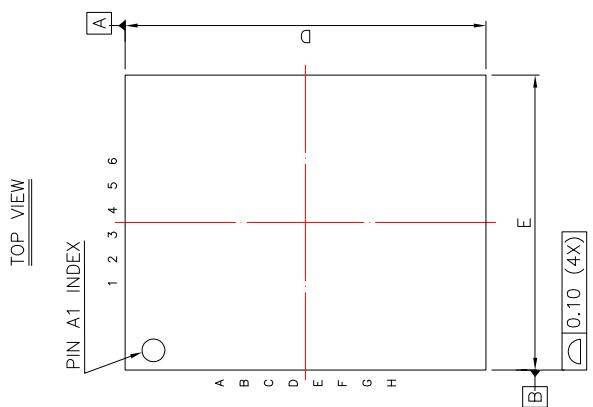
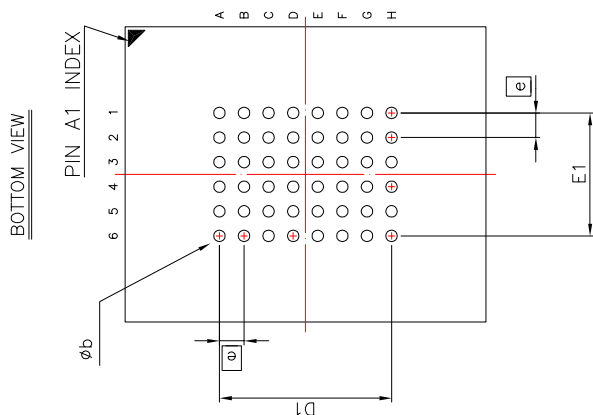
**Industrial Range: -40°C to +85°C**
**Voltage Range: 1.65V to 2.2V**

Speed (ns)	Order Part No.	Package
20	IS61WV20488ALL-20MI	48 mini BGA (9mm x 11mm)
	IS61WV20488ALL-20TI	TSOP (Type II)

**Automotive Range: -40°C to +125°C**
**Voltage Range: 2.4V to 3.6V**

Speed (ns)	Order Part No.	Package
10	IS64WV20488BLL-10MA3	48 mini BGA (9mm x 11mm)
	IS64WV20488BLL-10MLA3	48 mini BGA (9mm x 11mm), Lead-free
	IS64WV20488BLL-10TA3	TSOP (Type II)

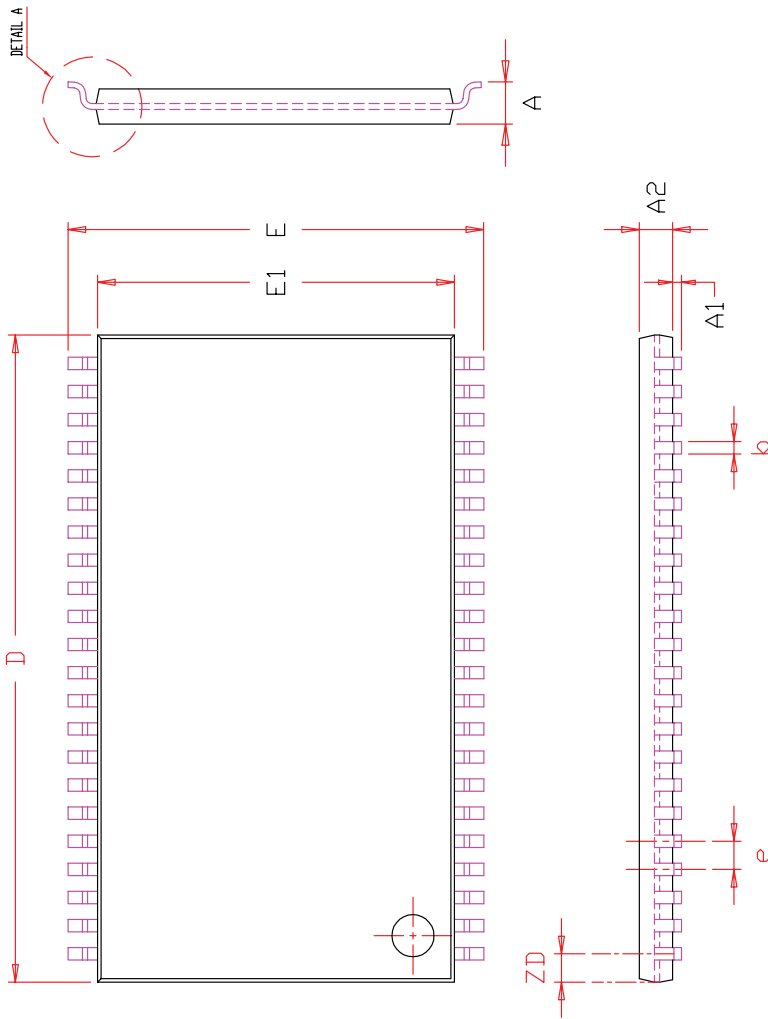
SYM.	DIMENSION (mm)			DIMENSION (INCH)		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	—	—	1.20	—	—	0.047
A1	0.20	—	0.30	0.008	—	0.012
b	0.30	0.35	0.40	0.012	0.014	0.016
D	10.90	11.00	11.10	0.429	0.433	0.437
D1	5.25	BSC	—	0.207	BSC	—
E	8.90	9.00	9.10	0.350	0.354	0.358
E1	—	3.75	BSC	—	0.148	BSC
⓪	—	0.75	BSC	—	0.030	BSC



**NOTE :**

1. CONTROLLING DIMENSION : MM.
2. Reference document : JEDEC MO-207

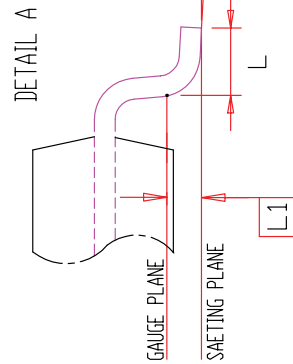
	TITLE	48L 9x11mm TF-BGA Package Outline	REV.	B	DATE	08/21/2008
--	-------	-----------------------------------	------	---	------	------------



SYMBOL	DIMENSION IN MM			DIMENSION IN INCH		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	1.00		1.20	0.039		0.047
A1	0.05		0.15	0.002		0.006
A2	0.95	1.00	1.05	0.037	0.039	0.041
b	0.30		0.45	0.012		0.018
D	18.28	18.41	18.54	0.720	0.725	0.730
E	11.56	11.76	11.96	0.455	0.463	0.471
E1	10.03	10.16	10.29	0.395	0.400	0.405
e	0.80 BSC.			0.031 BSC.		
L	0.40		0.69	0.016		0.027
L1	0.25 BSC.			0.010 BSC.		
ZD	0.805 REF.			0.032 REF.		
⊕	0		8°	0		8°

**NOTE :**

1. CONTROLLING DIMENSION : MM
2. DIMENSION D AND E1 DO NOT INCLUDE MOLD PROTRUSION.
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION/INTRUSION.



**TITLE** 44L 400mil TSOP-2  
Package Outline

**REV.** F

**DATE** 06/04/2008

**REV.** F

## Данный компонент на территории Российской Федерации

### Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

### Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: [info@moschip.ru](mailto:info@moschip.ru)

Skype отдела продаж:

moschip.ru

moschip.ru\_4

moschip.ru\_6

moschip.ru\_9